

first passage into said second internal cavity at a first temperature and to emit said second gas from said second internal cavity at a second temperature through a second passage, said first emitted gas and said second emitted gas varying the temperature of said processing area.

3. (Previously Presented) The system of Claim 2, wherein said second passage comprise a plurality of holes defined on a surface of said first and said second plates.

4. (Previously Presented) The system of Claim 2, wherein said first plate and said second plate comprise a heat source for heating said plate to a preselected temperature.

5. (Previously Presented) The system of Claim 2, wherein said first gas is taken from the group consisting of N<sub>2</sub>, He, H<sub>2</sub>, O<sub>2</sub>, Ar and gas mixtures containing He, H<sub>2</sub>, O<sub>2</sub>, Ar and N<sub>2</sub>.

6. (Previously Presented) The system of Claim 2, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.

7. (Canceled)

8. (Currently Amended) A system for wafer processing comprising:  
a chamber; and  
a first heatable plate and a second heatable plate at least one heatable plate  
positionable within said chamber, and defining a processing area therebetween, each  
of said heatable plates including:

an internal cavity defining an internal wall and configured to receive a gas;

means for heating said internal wall to a preselected temperature; and

an outlet portion defining a plurality of holes for emitting said gas to said processing area;